AMENDMENTS TO THE CLAIMS

The listing of claims below replaces all prior versions of claims in the application.

1. (Currently amended): A semiconductor device comprising a plurality of alignment marks formed over a semiconductor wafer,

each of the alignment marks comprising a micronized pattern,

the micronized pattern having a size smaller than a resolution limit of an alignment sensor of field image alignment detecting positions of the alignment marks, and

the micronized pattern having a pattern forming margin larger than ~~that of~~ a pattern forming margin which a device pattern formed over the semiconductor wafer has.

2. (Original): A semiconductor device according to claim 1, wherein
the micronized pattern is a line-and-space pattern.

3. (Original): A semiconductor device according to claim 2, wherein
each of lines constituting the line-and-space pattern are divided into a broken line having a plurality of segments.

4. (Original): A semiconductor device according to claim 3, wherein
positions of the divisions between the plurality of segments of the lines are offset from those of the divisions between the plurality of segments of their adjacent lines.

5-12. (Cancelled)

13. (Currently amended): A semiconductor device comprising a plurality of alignment marks formed over a semiconductor wafer,

each of the alignment marks being divided by a micronized line-and-space pattern into a plurality of lines extending along a first direction, and

each of the plural lines being divided into a broken line having a plurality of segments which are arranged in the first direction only.

14. (Original): A semiconductor device according to claim 13, wherein

positions of the divisions between the plurality of segments of the lines are offset from those of the divisions between the plurality of segments of their adjacent lines.

15. (Currently amended): A semiconductor device according to claim 13, wherein

a margin ~~for forming~~ in which the micronized pattern ~~to be formed in~~ is formed is larger than a margin for a device pattern to be formed on the semiconductor wafer.

16. (Currently amended): A semiconductor device according to claim 14, wherein

a margin ~~for forming~~ in which the micronized pattern ~~to be formed in~~ is formed is larger than a margin for a device pattern to be formed on the semiconductor wafer.